

Helping Customers Innovate, Improve & Grow



Features

- Radiation Tolerant
- Small footprint
- Frequency Range: 0.3 MHZ to 150 MHZ
- Previous Model: C2501

Applications

- Reference clock for space and satellite
- Military airborne and mobile systems

Performance Specifications

Parameter	Min	Тур	Мах	Units	Condition	
Frequency Stabilities ¹						
vs. operating temperature range (referenced to +25°C)	-10 -4 -2 -1		+10 +4 +2 +1	ppm ppm ppm ppm	-55 +105℃ -40 +85℃ -20 +70℃ 0 +50℃	
vs. aging / 1 year vs. aging / 10 years	-1 -5		+1 +5	ppm ppm		
Short Term Stability	-1		+1	ppb/sec		
		Suppl	y Voltag	je (Vs)		
Supply voltage	14.25	15.0	15.75	VDC		
Supply voltage	4.75	5.0	5.25	VDC		
Supply voltage	3.135	3.3	3.465	VDC		
Current			50 35	mA mA	ACMOS output Sinewave output	
RF Output						
Signal	CMOS					
Duty Cycle	40		60	%		
Rise\Fall time			+5	ns	(10% to 90%) with 2CMOS Loads	
Logic Level "0"			+0.5	V		
Logic Level "1"	Vcc -0.5V			V		

Performance Specifications

Parameter	Min	Тур	Max	Units	Condition
Signal	Sinewave				
Output Power	+7 +3			dBm dBm	standard
Harmonics			-20	dBc	(>75 MHz)
Sub-Harmonics			-20	dBc	(>75 MHz)
Spurious			-70	dBc	
	Frequency Tuning (EFC)				
Tuning Slope			Sufficie	nt to tune to	o nominal frequency for 10 years
		Additio	nal Para	meters	
Phase Noise (10MHz)			-95 -125 -145 -150 -150	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	10 Hz 100 Hz 1 KHz 10 KHz 100 KHz
Phase Noise (>75MHz)			-75 -105 -135 -145 -145	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	10 Hz 100 Hz 1 KHz 10 KHz 100 KHz
Weight			30	g	
	Ab	solute N	Maximu	m Ratings	
Supply voltage (Vs)	-0.5 -0.5		+7.0 +20	V V	(ACMOS) (Sinewave)
DC Input Current			+50	mA	
Lead Temperature (Soldering, 10 seconds)			300	°C	
Operable temperature range	-55		+125	°C	
Storage temperature range	-62		+125	°C	
				racteristic	S
Sine Vibration	Mil-STD-202, Method 204, TC "D"				
Random Vibration	Mil-STD-202, Method 214 TC "I-K" (15 minutes per axis)				
Shock	Mil-STD-202, Method 213, TC "F"				
Acceleration	Mil-STD-883, Method 2001, TC "A"				
Altitude	50,000 feet minimum to deep space				
Radiation	Radiation testing is not performed at the oscillator level, but these TCXOs have been acceptable for use in environments of up to 100K rads total dose, by analysis of the components used. The TTL Output TCXOs are assembled with all bipolar semiconductors. The CMOS Output TCXOs are assembled with all bipolar semiconductors with the exception of the ACMOS chip used to provide the CMOS output. A CMOS chip that is from a radation tested, certifi ed wafer lot can be provided if specified on the Purchase Order. A copy of the parts list and materials can be provided for customer review.				

Performance Specifications

Min Condition **Parameter** Тур Max Units **Manufacturing Information** QUARTZ CRYSTAL For the flight models, swept quartz shall be used in the manufacture of the crystals. For the Engineering models, non-swept quartz shall be used. TRAVELLERS Travellers or Process Cards are used in the manufacturing and testing of all Hi-Rel TCXOs and are available for customer review. Copies of these Travellers can be provided with the TCXOs at time of shipment if so specified on the purchase order. TRACEABILITY and HOMOGENEOUS MATERIAL Option Codes 'S' & 'R' only Manufacturing lot and date code information shall be recorded, by TCXO serial number, of every component and all materials used in the manufacture of that TCXO. Also all semiconductors used in the manufacture of any given Production Lot of TCXOs, shall be from the wafer and have the same manufacturing lot date code. A Production Lot, as defined by Corning, is all oscillators that have been kitted and assembled as a single group. After the initial kitting and assembly, this Production Lot may be divided into multiple sublots to facilitate alignment and test capacity and may be sealed at multiple times within a 13 week window. TEST DATA All Test Data is recorded by TCXO serial number. Copies of this data can be provided with the TCXOs at time of shipment if so specified on the purchase order.

REWORK

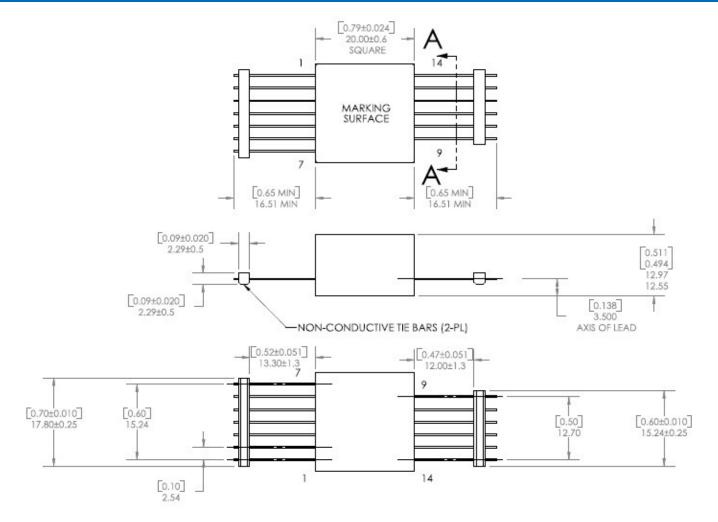
All rework follows the requirements of Mil-PRF-55310 Class 'S' for Option Code 'S' and Class 'B' for Option Codes 'R', 'B' and 'C'. The only exception is the Select-At-Test components may be replaced up to four times.

CONSTRUCTION, SCREENING & TESTING OPTIONS

NOTE: For Engineering or Prototype TCXOs requiring basic electrical testing only and no Screening, or Groups 'A' and 'B' Testing, use the code letter 'E'.

the code letter 'E'.				
Operation \ Code	"S"	"R"	"C"	"B"
Design, Construction & Component Screen (see Mfging Section)	Mil-PRF-55310 Class 'S'	Mil-PRF-55310 Class 'B'	Mil-PRF-55310 Class 'B'	Mil-PRF-55310 Class 'B'
Workmanship	M883, Method 2017 for Class 'S'	M883, Method 2017 for Class 'B'	M883, Method 2017 for Class 'B'	M883, Method 2017 for Class 'B'
Screening	Mil-PRF-55310 Class 'S'	Mil-PRF-55310 Class 'S'	Mil-PRF-55310 Class 'B' modified	Mil-PRF-55310 Class 'B'
Non-Destruct Wire Bond Pull	100%	100%	N/A	N/A
Internal Visual	M883, Method 2017 for Class 'S'	M883, Method 2017 for Class 'B'	M883, Method 2017 for Class 'B'	M883, Method 2017 for Class 'B'
Stabilization Bake	48 hrs minimum @ +150℃	48 hrs minimum @ +150°C	48 hrs minimum @ +150°C	48 hrs minimum @ +150°C
Thermal Shock	M883, Method 1011, TC 'A'	M883, Method 1011, TC 'A'	N/A	N/A
Constant Acceleration	M883, Method 2001, TC 'A' (5000 gs, Y1 Axis only)	M883, Method 2001, TC 'A' (5000 gs, Y1 Axis only)	M883, Method 2001, TC 'A' (5000 gs, Y1 Axis only)	M883, Method 2001, TC 'A' (5000 gs, Y1 Axis only)
Seal Test (fine & gross)	100%	100%	100%	100%
PIND	M883, Method 2020, TC 'B'	M883, Method 2020, TC 'B'	M883, Method 2020, TC 'B'	N/A
Electrical Test Frequency, Output levels, Input Current	@ +25°C only	@ +25°C only	@ +25°C only	@ +25°C only
Burn-In (Powered with load)	+125°C for 240 hours	+125°C for 240 hours	+125°C for 160 hours	+125°C for 160 hours
Electrical Test Frequency, Output levels, Input Current	@ +25°C & Temp Extremes specifi ed in Table II	@ +25°C & Temp Extremes specifi ed in Table II	@ +25°C & Temp Extremes specifi ed in Table II	@ +25°C & Temp Extremes specifi ed in Table II
PDA	2% applies to Input Current @ +25°C	2% applies to Input Current @ +25°C	10% applies to Input Current @ +25°C	10% applies to Input Current @ +25°C
Radiographic	M883, Method 2012	M883, Method 2012	N/A	N/A
Group'A'	100%	100%	Sample per Mil-PRF-55310	Sample per Mil-PRF-55310
Group 'B' (30 day Aging @ +70°C)	100%	100%	Sample per Mil-PRF-55310	Sample per Mil-PRF-55310

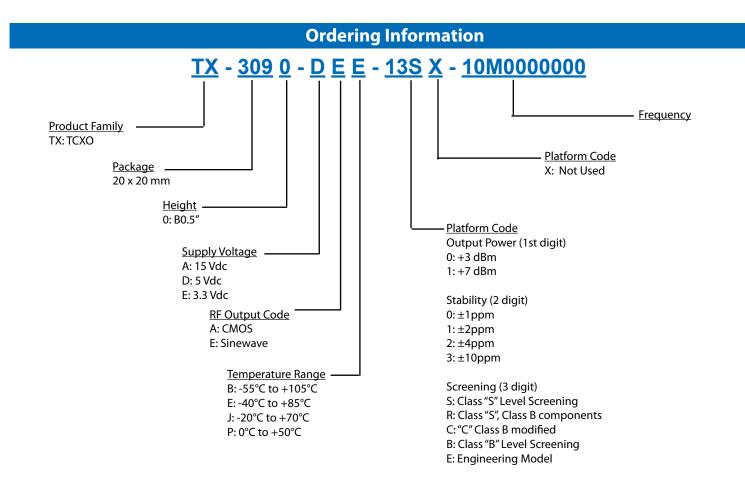
Outline Drawing / Enclosure



Dimensions in [inches] mm

	Туре В	
Code	Height "H"	Pin Length "L"
0	0.5″	0.65″

Pin Connections				
1,3,7,12,14	12,14 Ground			
2	Supply			
4,5,9,10,11	No Connection			
6	External Frequency Control			
13	RF Output			



Notes:

- 1. Contact factory for improved stabilities or additional product options. Not all options and codes are available at all frequencies.
- 2. Unless other stated all values are valid after warm-up time and refer to typical conditions for supply voltage, frequency control voltage, load, temperature (25°C).
- 3. Phase noise degrades with increasing output frequency.
- 4. Subject to technical modification.
- 5. Contact factory for availability.

For Additional Information, Please Contact

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